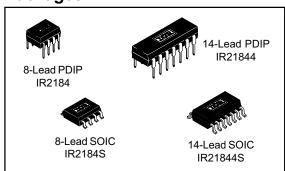


#### HALF-BRIDGE DRIVER

#### **Features**

- Floating channel designed for bootstrap operation Fully operational to +600V Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V and 5V input logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5V offset.
- Lower di/dt gate driver for better noise immunity
- Output source/sink current capability 1.4A/1.8A
- Also available LEAD-FREE (PbF)

#### **Packages**



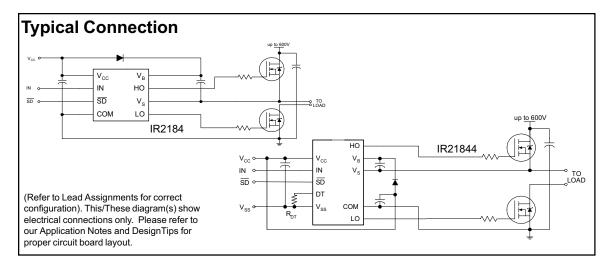
#### Description

The IR2184(4)(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a

#### IR2181/IR2183/IR2184 Feature Comparison

Part	Input logic	Cross- conduction prevention logic	Dead-Time	Ground Pins	Ton/Toff		
2181	HIN/LIN	no	no none	COM	180/220 ns		
21814	TIIIN/LIIN	no none		no none		VSS/COM	100/220113
2183	HIN/LIN	yes	Internal 500ns	COM	180/220 ns		
21834	I IIIN/LIIN	yes	Program 0.4 ~ 5 us	VSS/COM	100/220 115		
2184	IN/SD	Vec	Internal 500ns	COM	680/270 ns		
21844	114/30	yes	Program 0.4 ~ 5 us	VSS/COM	000/2/0118		

high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.



#### **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V <sub>B</sub>	High side floating absolute voltage	-0.3	625		
Vs	High side floating supply offset voltage	V <sub>B</sub> - 25	V <sub>B</sub> + 0.3		
V <sub>HO</sub>	High side floating output voltage		Vs - 0.3	V <sub>B</sub> + 0.3	
V <sub>CC</sub>	Low side and logic fixed supply voltage		-0.3	25	
V <sub>LO</sub>	Low side output voltage		-0.3	V <sub>CC</sub> + 0.3	V
DT	Programmable dead-time pin voltage (IR21	844 only)	V <sub>SS</sub> - 0.3	V <sub>CC</sub> + 0.3	
VIN	Logic input voltage (IN & SD)		V <sub>SS</sub> - 0.3	V <sub>SS</sub> + 5	
V <sub>SS</sub>	Logic ground (IR21844 only)		V <sub>CC</sub> - 25	V <sub>CC</sub> + 0.3	
dV <sub>S</sub> /dt	Allowable offset supply voltage transient		_	50	V/ns
P <sub>D</sub>	Package power dissipation @ T <sub>A</sub> ≤ +25°C	(8-lead PDIP)	_	1.0	
		(8-lead SOIC)	_	0.625	1
		(14-lead PDIP)	_	1.6	W
		(14-lead SOIC)	_	1.0	
Rth <sub>JA</sub>	Thermal resistance, junction to ambient	(8-lead PDIP)	_	125	
		(8-lead SOIC)	_	200	
		(14-lead PDIP)	_	75	°C/W
		(14-lead SOIC)	_	120	Ţ
TJ	Junction temperature		_	150	
Ts	Storage temperature		-50	150	°C
TL	Lead temperature (soldering, 10 seconds)		_	300	Ī

#### **Recommended Operating Conditions**

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The Vs and Vss offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	V <sub>S</sub> + 10	V <sub>S</sub> + 20	
Vs	High side floating supply offset voltage	Note 1	600	
V <sub>HO</sub>	High side floating output voltage	Vs	V <sub>B</sub>	
V <sub>CC</sub>	Low side and logic fixed supply voltage	10	20	
V <sub>LO</sub>	Low side output voltage	0	Vcc	V
V <sub>IN</sub>	Logic input voltage (IN & SD)	V <sub>SS</sub>	V <sub>SS</sub> + 4	
DT	Programmable dead-time pin voltage (IR21844 only)	V <sub>SS</sub>	Vcc	
V <sub>SS</sub>	Logic ground (IR21844 only)	-5	5	
TA	Ambient temperature	-40	125	°C

Note 1: Logic operational for V<sub>S</sub> of -5 to +600V. Logic state held for V<sub>S</sub> of -5V to -V<sub>BS</sub>. (Please refer to the Design Tip DT97-3 for more details).

Note 2: IN and SD are internally clamped with a 5.2V zener diode.

#### **Dynamic Electrical Characteristics**

V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, V<sub>SS</sub> = COM, C<sub>L</sub> = 1000 pF, T<sub>A</sub> = 25°C, DT = VSS unless otherwise specified.

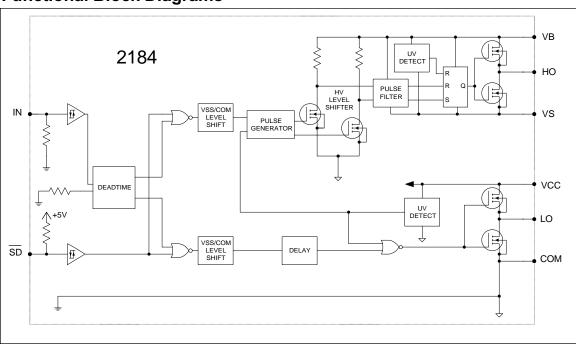
Symbol	Definition		Тур.	Max.	Units	<b>Test Conditions</b>
ton	Turn-on propagation delay	_	680	900		V <sub>S</sub> = 0V
toff	Turn-off propagation delay	_	270	400		V <sub>S</sub> = 0V or 600V
tsd	Shut-down propagation delay	_	180	270		
MTon	Delay matching, HS & LS turn-on	_	0	90	nsec	
MToff	Delay matching, HS & LS turn-off	_	0	40		
t <sub>r</sub>	Turn-on rise time	_	40	60		V <sub>S</sub> = 0V
tf	Turn-off fall time	_	20	35		V <sub>S</sub> = 0V
DT	Deadtime: LO turn-off to HO turn-on(DTLO-HO) &	280	400	520		RDT= 0
	HO turn-off to LO turn-on (DTHO-LO)	4	5	6	μsec	RDT = 200k
MDT	Deadtime matching = DTLO - HO - DTHO-LO	_	0	50	ncoc	RDT=0
		_	0	600	nsec	RDT = 200k

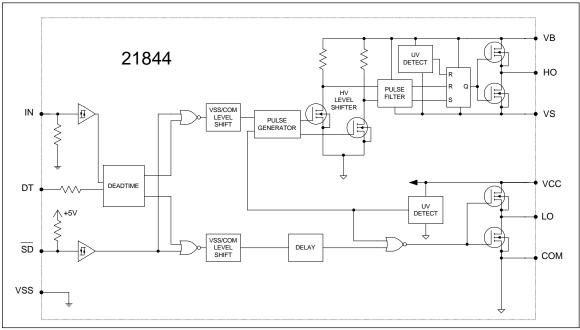
#### **Static Electrical Characteristics**

 $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V,  $V_{SS}$  = COM, DT=  $V_{SS}$  and  $T_A$  = 25°C unless otherwise specified. The  $V_{IL}$ ,  $V_{IH}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}$ /COM and are applicable to the respective input leads: IN and  $\overline{SD}$ . The  $V_O$ ,  $I_O$  and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition		Тур.	Max.	Units	<b>Test Conditions</b>
V <sub>IH</sub>	Logic "1" input voltage for HO & logic "0" for LO	2.7	_	_		V <sub>CC</sub> = 10V to 20V
V <sub>IL</sub>	Logic "0" input voltage for HO & logic "1" for LO		_	0.8		V <sub>CC</sub> = 10V to 20V
V <sub>SD,TH+</sub>	SD input positive going threshold	2.7	_	_	V	V <sub>CC</sub> = 10V to 20V
V <sub>SD,TH</sub> -	SD input negative going threshold	_	_	0.8		V <sub>CC</sub> = 10V to 20V
V <sub>OH</sub>	High level output voltage, V <sub>BIAS</sub> - V <sub>O</sub>	_	_	1.2		I <sub>O</sub> = 0A
V <sub>OL</sub>	Low level output voltage, VO	_	_	0.1		I <sub>O</sub> = 0A
I <sub>LK</sub>	Offset supply leakage current	_	_	50		V <sub>B</sub> = V <sub>S</sub> = 600V
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	20	60	150	μA	V <sub>IN</sub> = 0V or 5V
IQCC	Quiescent V <sub>CC</sub> supply current	0.4	1.0	1.6	mA	V <sub>IN</sub> = 0V or 5V
I <sub>IN+</sub>	Logic "1" input bias current		25	60	μA	IN = 5V, SD = 0V
I <sub>IN-</sub>	Logic "0" input bias current	_	_	1.0	μΑ	$IN = 0V, \overline{SD} = 5V$
V <sub>CCUV+</sub> V <sub>BSUV+</sub>	V <sub>CC</sub> and V <sub>BS</sub> supply undervoltage positive going threshold	8.0	8.9	9.8		
V <sub>CCUV</sub> - V <sub>BSUV</sub> -	$V_{CC}$ and $V_{BS}$ supply undervoltage negative going threshold	7.4	8.2	9.0	.,	
VCCUVH	Hysteresis	0.3	0.7	_	V	
V <sub>BSUVH</sub>						
I <sub>O+</sub>	Output high short circuit pulsed current	1.4	1.9			V <sub>O</sub> = 0V,
					_	PW ≤ 10 µs
I <sub>O-</sub>	Output low short circuit pulsed current	1.8	2.3	-	Α	V <sub>O</sub> = 15V,
						PW ≤ 10 µs

### **Functional Block Diagrams**

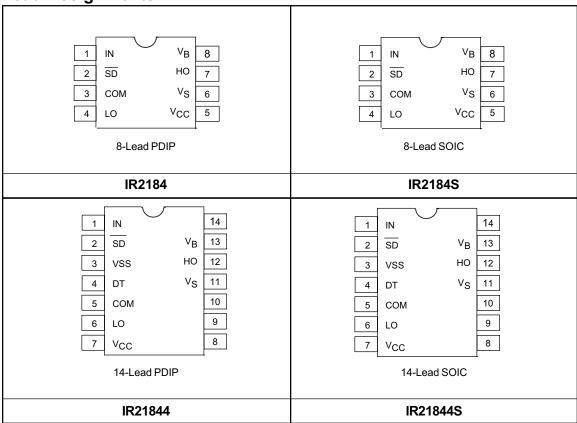




#### **Lead Definitions**

Symbol	Description		
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO (referenced to COM		
	for IR2184 and VSS for IR21844)		
SD	Logic input for shutdown (referenced to COM for IR2184 and VSS for IR21844)		
DT	Programmable dead-time lead, referenced to VSS. (IR21844 only)		
VSS	Logic Ground (21844 only)		
V <sub>B</sub>	High side floating supply		
НО	High side gate drive output		
Vs	High side floating supply return		
V <sub>CC</sub>	Low side and logic fixed supply		
LO	Low side gate drive output		
СОМ	Low side return		

### **Lead Assignments**



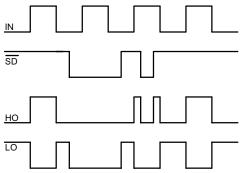


Figure 1. Input/Output Timing Diagram

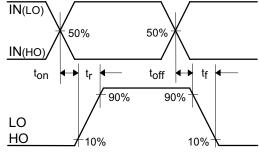


Figure 2. Switching Time Waveform Definitions

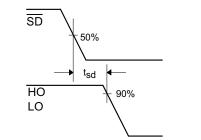


Figure 3. Shutdown Waveform Definitions

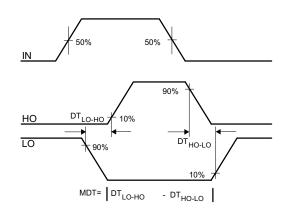


Figure 4. Deadtime Waveform Definitions

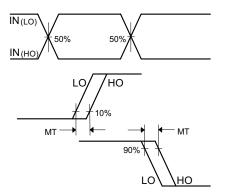


Figure 5. Delay Matching Waveform Definitions

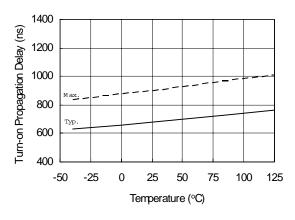


Figure 4A. Turn-on Propagation Delay vs. Temperature

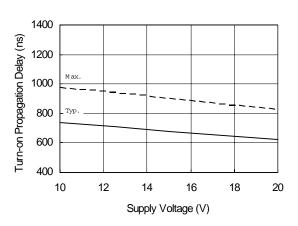


Figure 4B. Turn-on Propagation Delay vs. Supply Voltage

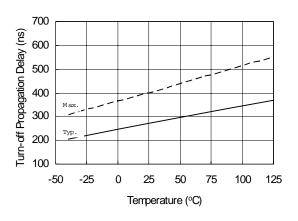


Figure 5A. Turn-off Propagation Delay vs. Temperature

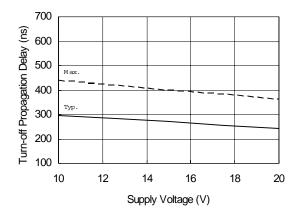


Figure 5B. Turn-off Propagation Delay vs. Supply Voltage

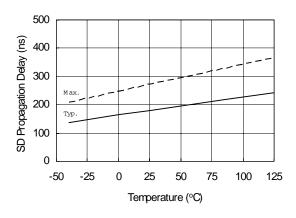


Figure 6A. SD Propagation Delay vs. Temperature

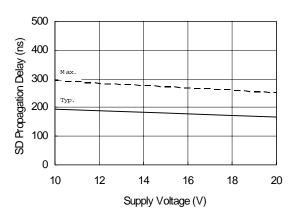


Figure 6B. SD Propagation Delay vs. Supply Voltage

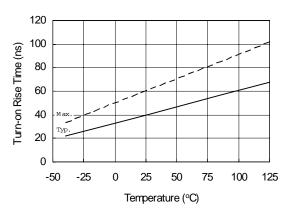


Figure 7A. Turn-on Rise Time vs. Temperature

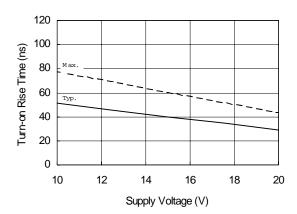


Figure 7B. Turn-on Rise Time vs. Supply Voltage

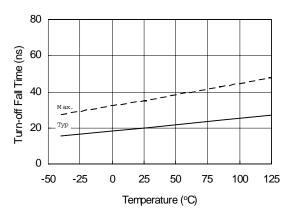


Figure 8A. Turn-off Fall Time vs. Temperature

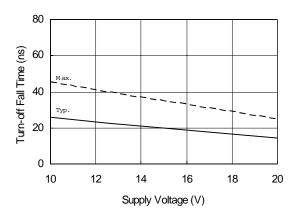


Figure 8B. Turn-off Fall Time vs. Supply Voltage

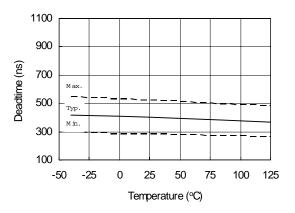


Figure 9A. Deadtime vs. Temperature

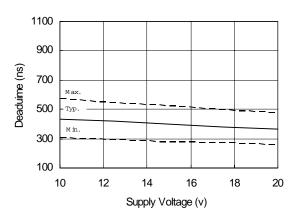


Figure 9B. Deadtime vs. Supply Voltage

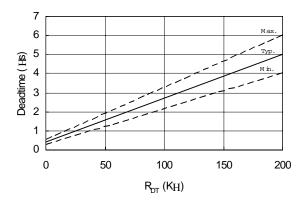


Figure 9C. Deadtime vs.  $R_{\rm DT}$ 

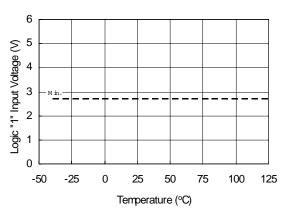


Figure 10A. Logic "1" Input Voltage vs. Temperature

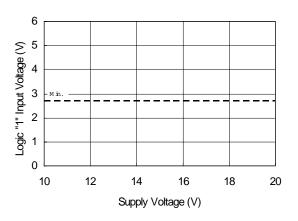


Figure 10B. Logic "1" Input Voltage vs. Supply Voltage

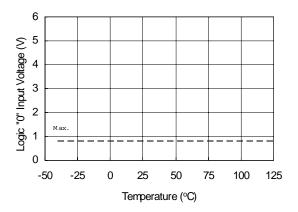


Figure 11A. Logic "0" Input Voltage vs. Temperature

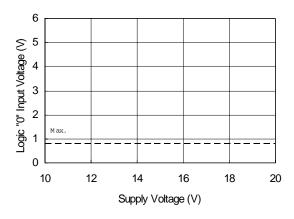


Figure 11B. Logic "0" Input Voltage vs. Supply Voltage

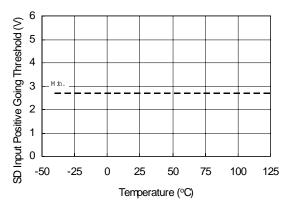


Figure 12A. SD Input Positive Going Threshold vs. Temperature

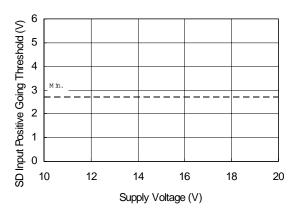


Figure 12B. SD Input Positive Going Threshold vs. Supply Voltage

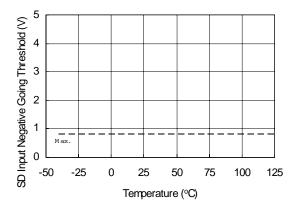


Figure 13A. SD Input Negative Going Threshold vs. Temperature

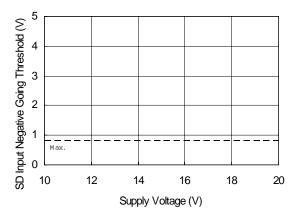


Figure 13B. SD Input Negative Going Threshold vs. Supply Voltage

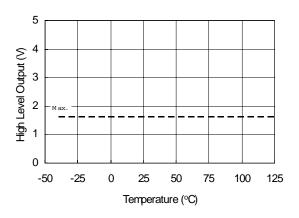


Figure 14A. High Level Output vs. Temperature

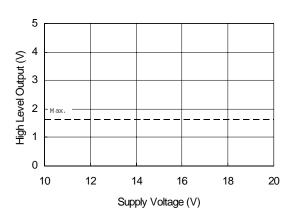


Figure 14B. High Level Output vs. Supply Voltage

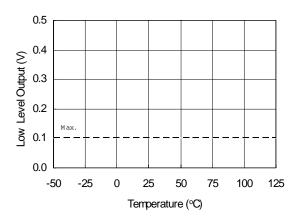


Figure 15A Low Level Output vs. Temperature

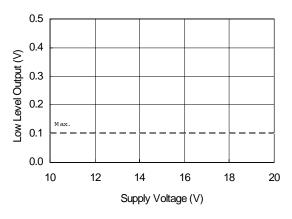


Figure 15B. Low Level Output vs. Supply Voltage

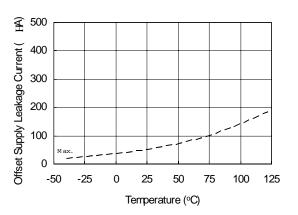


Figure 16A. Offset Supply Leakage Current vs.
Temperature

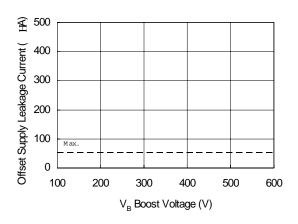


Figure 16B. Offset Supply Leakage Current vs.  $V_{\rm B}$  Boost Voltage

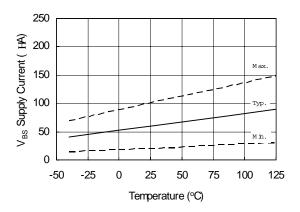


Figure 17A. V<sub>BS</sub> Supply Current vs. Temperature

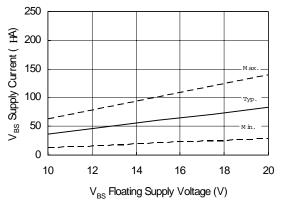


Figure 17B.  $\rm V_{BS}$  Supply Current vs.  $\rm V_{BS}$  Floating Supply Voltage

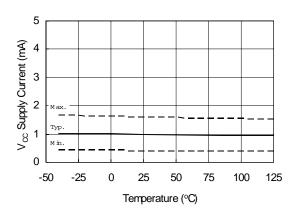


Figure 18A.  $V_{\rm CC}$  Supply Current vs. Temperature

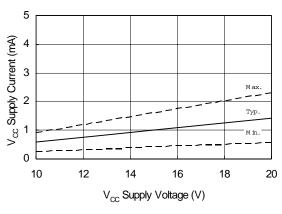


Figure 18B.  $V_{\rm CC}$  Supply Current vs.  $V_{\rm CC}$  Supply Voltage

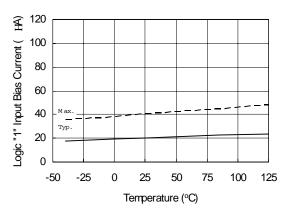


Figure 19A. Logic "1" Input Bias Current vs. Temperature

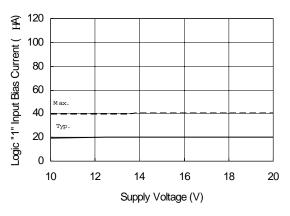


Figure 19B. Logic "1" Input Bias Current vs. Supply Voltage

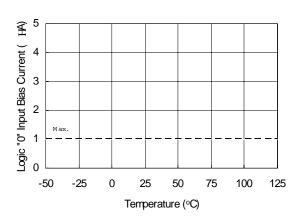


Figure 20A. Logic "0" Input Bias Current vs. Temperature

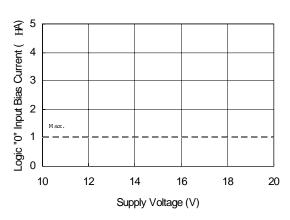


Figure 20B. Logic "0" Input Bias Current vs. Supply Voltage

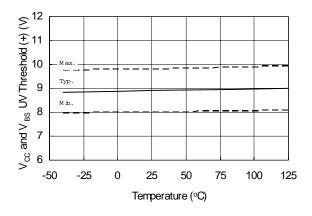


Figure 21.  $V_{CC}$  and  $V_{BS}$  Undervoltage Threshold (+) vs. Temperature

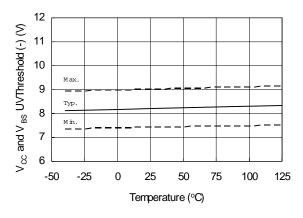


Figure 22.  $\rm V_{CC}$  and  $\rm V_{BS}$  Undervoltage Threshold (-) vs. Temperature

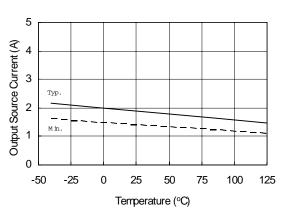


Figure 23A. Output Source Current vs. Temperature

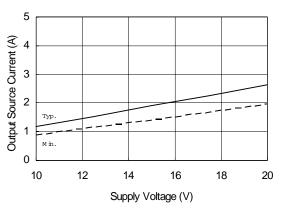


Figure 23B. Output Source Current vs. Supply Voltage

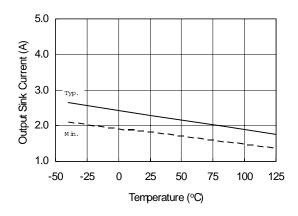


Figure 24A. Output Sink Current vs. Temperature

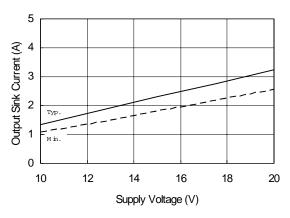


Figure 24B. Output Sink Current vs. Supply Voltage

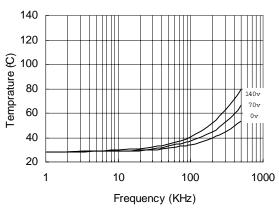


Figure 21.  $\mathbb{R}$  2181 vs. Frequency ( $\mathbb{R}$  FBC 20),  $R_{\text{gabs}} = 33 \Omega, V_{\text{CC}} = 15 V$ 

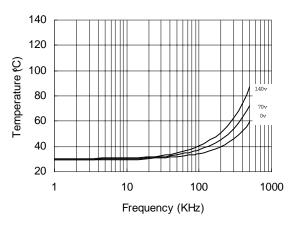


Figure 22.R2181 vs.Frequency (RFBC30),  $R_{\rm gab} = 22 _{ { \Omega }}, V_{\rm CC} = 15 V$ 

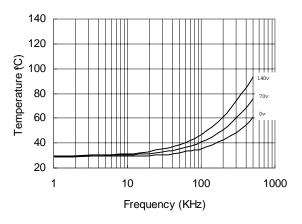


Figure 23.  $\mathbb{R}$  2181 vs. Frequency ( $\mathbb{R}$  FBC 40),  $R_{\text{gate}} = 15 \Omega, V_{\text{CC}} = 15 V$ 

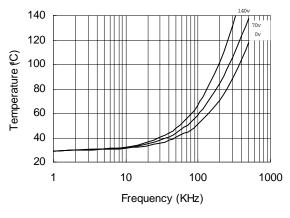


Figure 24.  $\mathbb{R}$  2181 vs. Frequency ( $\mathbb{R}$  FPE50),  $R_{\text{gabs}} = 10_{\Omega}, V_{\text{CC}} = 15 V$ 

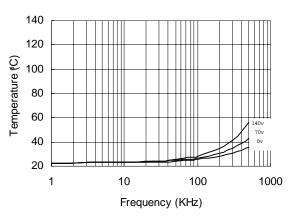


Figure 25.R21814 vs.Frequency (RFBC 20),  $R_{\rm gate} = 33 \Omega \text{,V}_{\rm CC} = 15 \text{V}$ 

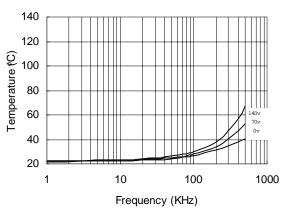


Figure 26.R21814 vs.Frequency (RFBC30),  $R_{_{\tt cabe}} = 22 {\Omega}, V_{_{\tt CC}} = 15 V$ 

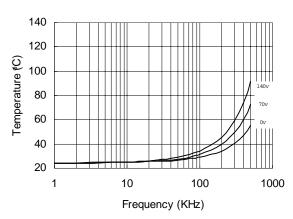


Figure 27.R21814 vs.Frequency (RFBC 40),  $R_{\rm gate} = 15 \Omega, V_{\rm CC} = 15 V$ 

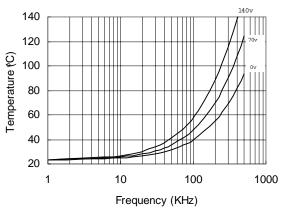


Figure 28.R21814 vs.Frequency (RFPE50),  $R_{\rm gate} = 10 \, \Omega \, , V_{\rm CC} = 15 V \label{eq:RFPE50}$ 

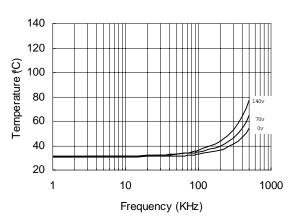


Figure 29.R2181s vs.Frequency (RFBC20),  $R_{\rm gate} = 33 \Omega, V_{\rm CC} = 15 V$ 

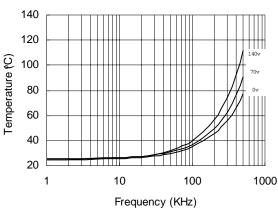


Figure 30.R2181s vs.Frequency (RFBC30),  $R_{\rm gate} = 22 \Omega \text{, V}_{\rm CC} = 15 \text{V}$ 

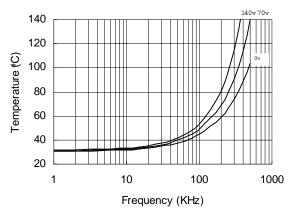


Figure 31.  $\mathbb{R}$  2181s vs. Frequency ( $\mathbb{R}$  FBC 40),  $\mathbf{R}_{\text{gate}} = 15 \mathbf{\Omega}, \mathbf{V}_{\text{CC}} = 15 \mathbf{V}$ 

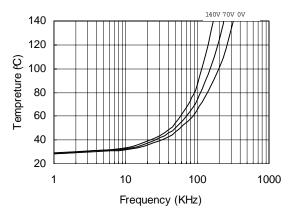


Figure 32. IR2181s vs. Frequency (IRFPE50),  $R_{\text{oate}} {=} 10 \Omega, \, V_{\text{CC}} {=} 15 \text{V}$ 

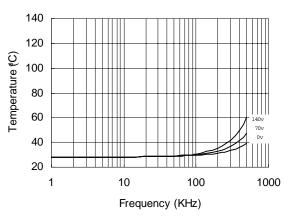


Figure 33. IR21814s vs. Frequency (IRFBC20),  $R_{oate}$ =33 $\Omega$ ,  $V_{cc}$ =15V

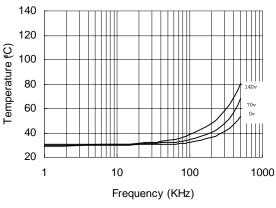


Figure 34. IR21814s vs. Frequency (IRFBC30),  ${\rm R_{gate}}{=}22\underline{\Omega},\,{\rm V_{CC}}{=}15{\rm V}$ 

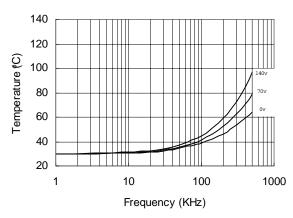


Figure 35. IR21814s vs. Frequency (IRFBC40),  $\rm R_{oate} = 15\Omega,\, \rm V_{CC} = 15V$ 

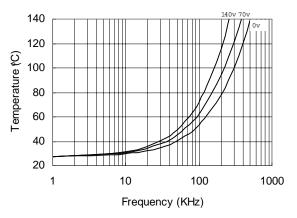
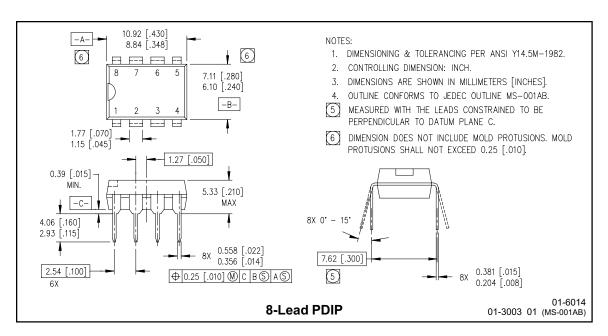
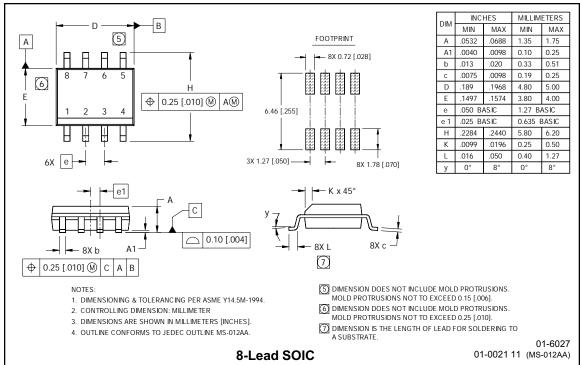
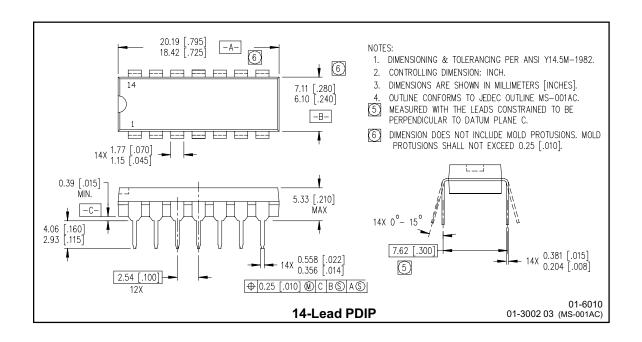
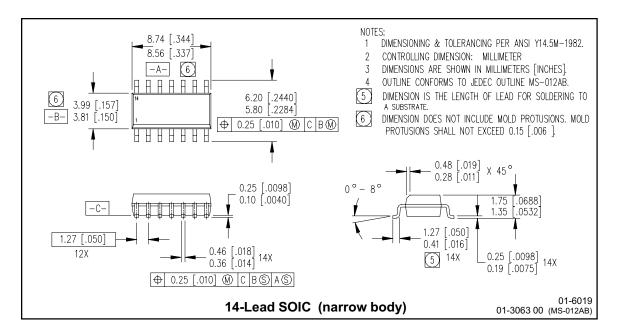


Figure 36. IR21814s vs. Frequency (IRFPE50),  $\rm R_{gate} {=} 10 \Omega, \, \rm V_{CC} {=} 15 V$ 

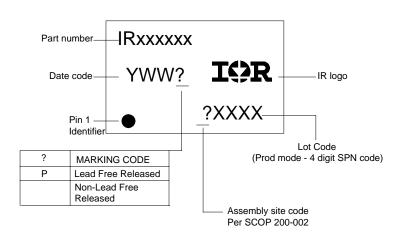








#### LEADFREE PART MARKING INFORMATION



#### ORDER INFORMATION

#### **Basic Part (Non-Lead Free)**

8-Lead PDIP IR2184 order IR2184 8-Lead SOIC IR2184S order IR2184S 14-Lead PDIP IR21844 order IR21844 14-Lead SOIC IR21844 order IR21844S

#### Leadfree Part

8-Lead PDIP IR2184 order IR2184PbF 8-Lead SOIC IR2184S order IR2184SPbF 14-Lead PDIP IR21844 order IR21844PbF 14-Lead SOIC IR21844 order IR21844SPbF

# International TOR Rectifier

Thisproduct has been designed and qualified for the industrial market.

Qualification Standards can be found on IR's Web Site http://www.irf.com

Data and specifications subject to change without notice.

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

4/4/2006